

	Type	Hits	Search Text	DBs	Time Stamp
21	BRS	31	(photoelectric\$5 and (amorphous near10 (silicon: adj (carbide and nitride)))) and boron	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 09:22

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	50	(ken near2 kitamura) or (yoshinori near2 hatanaka)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/26 12:48
2	BRS	277	photoelectric\$5 and (silicon adj (carbide and nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/26 14:25
3	BRS	7	((KITAMURA near2 KEN) or (HATANAKA near2 YOSHINORI)) and (amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/26 13:43
4	BRS	198	(photoelectric\$5 and (silicon adj (carbide and nitride))) and (amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/26 13:46
5	BRS	44	((photoelectric\$5 and (silicon adj (carbide and nitride))) and (amorphous)) and (dark adj current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/26 13:47
6	BRS	67	photoelectric\$5 and (amorphous near10 (silicon) near30 multipl\$8)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 09:16
7	BRS	209	photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 polycrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:50
8	BRS	60	photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 microcrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:49
9	BRS	108	photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:44
10	BRS	59	photoelectric\$5 and (amorphous near10 (silicon) adj (carbide and nitride)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 09:22
11	BRS	904	photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:44
12	BRS	2	(photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 polycrystalline)) and (photoelectric\$5 and (amorphous near10 (silicon) adj (carbide and nitride)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:45
13	BRS	2	(photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 microcrystalline)) and (photoelectric\$5 and (amorphous near10 (silicon) adj (carbide and nitride)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:49
14	BRS	60	photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 microcrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:55
15	BRS	0	photoelectric\$5 and (substrate near10 (microcrystalline and polycrystalline and monocrystalline and metal))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:56
16	BRS	0	photoelectric\$5 and (substrate near10 (microcrystalline and polycrystalline))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:56
17	BRS	0	(substrate near10 (microcrystalline and polycrystalline and monocrystalline and metal))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 08:57
18	BRS	3	(photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 monocrystalline)) and (photoelectric\$5 and (amorphous near10 (silicon) adj (carbide and nitride)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 09:02
19	BRS	19	(photoelectric\$5 and (amorphous near10 (silicon)) and (substrate near10 metal)) and (photoelectric\$5 and (amorphous near10 (silicon) adj (carbide and nitride)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 09:06
20	BRS	3	photoelectric\$5 and (amorphous near10 (silicon)) and ((electric adj field) near5 layer near5 (reduction or reducing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/30 09:17